

FORM PTO-1449

Docket Number (Optional)  
81784.0182Application Number  
09/148,606INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

(Use several sheets if necessary)

Applicant

Kiyoshi YONEDA et al.

Filing Date

September 4, 1998

Group Art Unit

2774

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AZ	4	4	6	6	1	7	9	8/84	Kasten	29	576	10/19/82
AZ	5	1	4	5	8	0	8	9/92	Sameshima et al.	437	174	8/1/94
AZ	5	5	2	9	9	5	1	6/96	Noguchi et al.	437	RE74	11/1/94
AZ	5	9	6	0	3	2	3	9/99	Wakita et al.	438	795	10/17/97

FEB 09 2001  
Technology Center 2600

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	Translation	
												YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AZ	Kubo et al., "Characteristics of Polycrystalline-Si Thin Film Transistors Fabricated by Excimer Laser Annealing Method", IEEE Transactions on Electron Devices, Oct. 1994, pp. 1876-1879
AZ	Kohno et al., "High Performance Poly-Si TFTs Fabricated Using Pulsed Laser Annealing and Remote Plasma CVD With Low Temperature Processing", IEEE Transactions on Electron Devices, Feb. 1995, pp. 251-257
AZ	Kuriyama, "Excimer Laser Crystallization of Silicon Films for AMLCDs", AMLCK Second International Workshop on Active Matrix Liquid Crystal Displays, Sept. 1995, pp. 87-92

EXAMINER

AZ Zani

DATE CONSIDERED

08-09-01

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.